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# 2SC1921

Silicon NPN Triple Diffused

# HITACHI

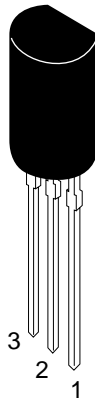
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## Application

- High frequency high voltage amplifier
- Video output

## Outline

TO-92MOD



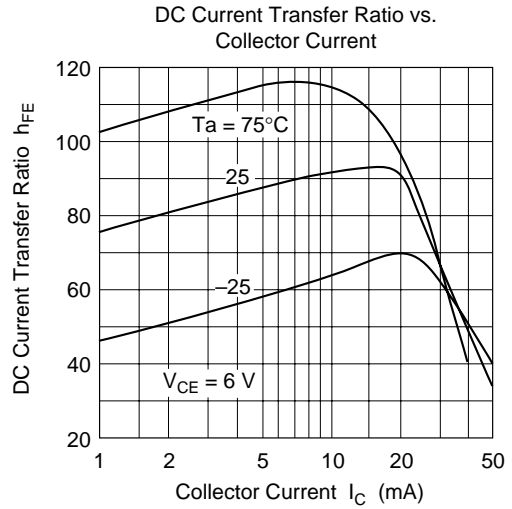
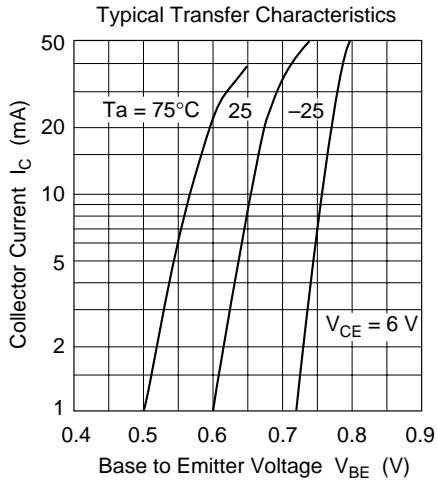
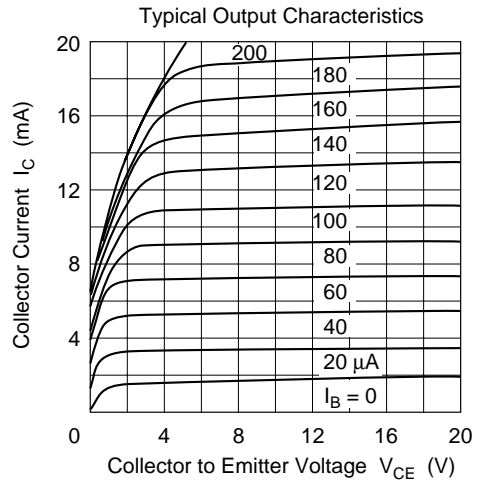
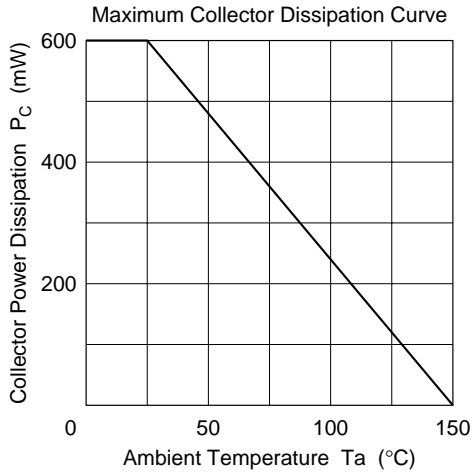
1. Emitter
2. Collector
3. Base

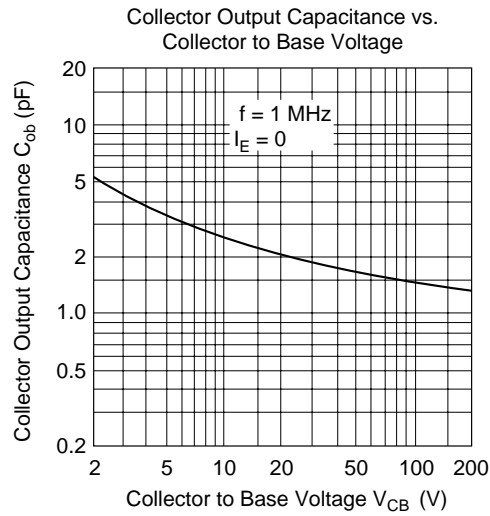
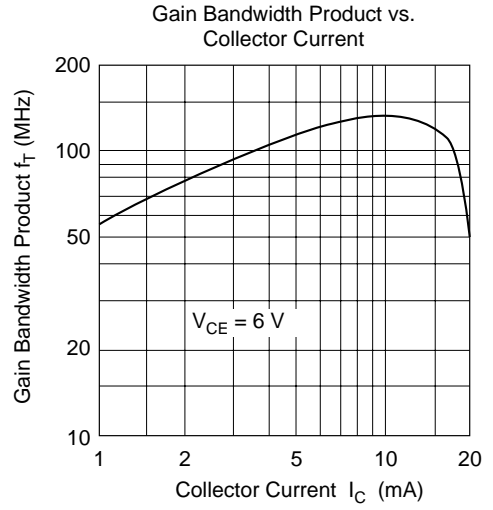
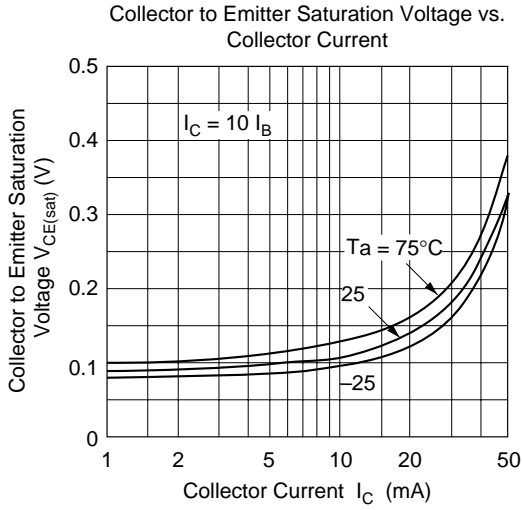
**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

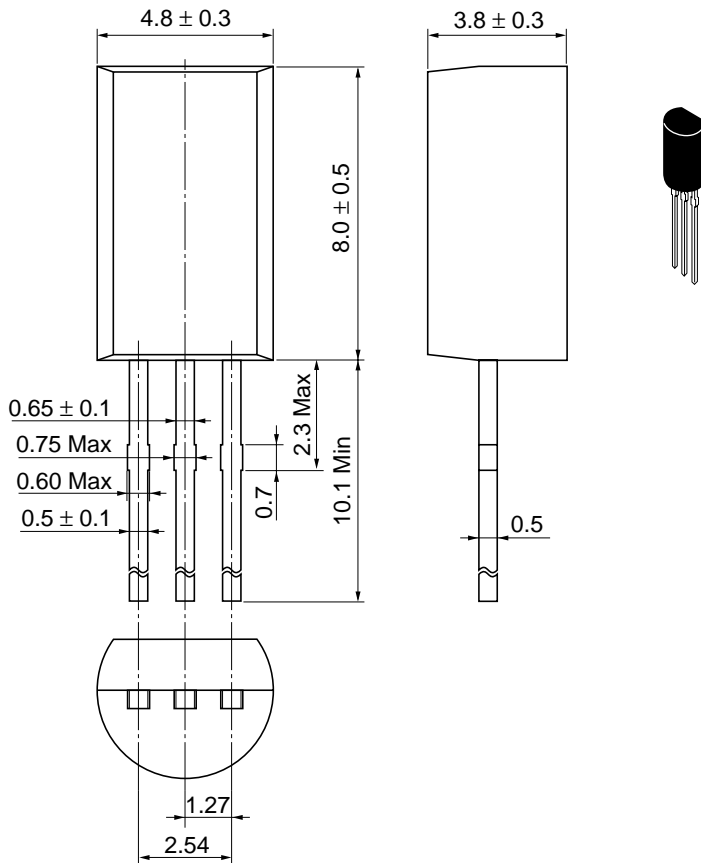
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	250	V
Collector to emitter voltage	$V_{\text{CEO}}$	200	V
Emitter to base voltage	$V_{\text{EBO}}$	5	V
Collector current	$I_{\text{C}}$	50	mA
Collector power dissipation	$P_{\text{C}}$	600	mW
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	250	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$ , $I_{\text{E}} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	200	—	—	V	$I_{\text{C}} = 1 \text{ mA}$ , $R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	5	—	—	V	$I_{\text{E}} = 10 \mu\text{A}$ , $I_{\text{C}} = 0$
Collector cutoff current	$I_{\text{CEO}}$	—	—	1.0	$\mu\text{A}$	$V_{\text{CE}} = 120 \text{ V}$ , $R_{\text{BE}} = \infty$
DC current transfer ratio	$h_{\text{FE}}$	30	—	300		$V_{\text{CE}} = 6 \text{ V}$ , $I_{\text{C}} = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	—	—	1.0	V	$I_{\text{C}} = 10 \text{ mA}$ , $I_{\text{B}} = 1 \text{ mA}$
Gain bandwidth product	$f_{\text{T}}$	60	130	—	MHz	$V_{\text{CE}} = 6 \text{ V}$ , $I_{\text{C}} = 10 \text{ mA}$
Collector output capacitance	$C_{\text{ob}}$	—	3	4	pF	$V_{\text{CB}} = 6 \text{ V}$ , $I_{\text{E}} = 0$ , $f = 1 \text{ MHz}$







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
             Europe                 : <http://www.hitachi-eu.com/hel/ecg>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1>(408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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